

2SA966 TRANSISTOR (PNP)

FEATURE

Power dissipation

$$P_{CM}: 0.9 \text{ W} (T_{amb}=25^{\circ}\text{C})$$

Collector current

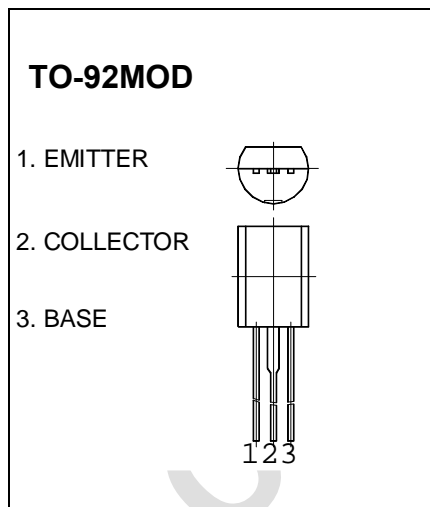
$$I_{CM}: -1.5 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO}: -30 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^{\circ}\text{C} \text{ to } +150^{\circ}\text{C}$$



ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -1\text{mA}, I_E = 0$	-30		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10\text{mA}, I_B = 0$	-30		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -1\text{mA}, I_C = 0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -30\text{V}, I_E = 0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{V}, I_C = 0$		-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -2\text{V}, I_C = -500\text{mA}$	100	320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1.5\text{A}, I_B = -0.03\text{A}$		-2	V
Base-emitter voltage	V_{BE}	$I_C = -500\text{mA}, V_{CE} = -2\text{V}$		-1	V
Transition frequency	f_T	$V_{CE} = -2\text{V}, I_C = -500\text{mA}$	100		MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	100-200	160-320